



DMN2005UFG

20V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C (t<10s)		
20V	$4.6m\Omega @ V_{GS} = 4.5V$	24.1A		
200	$8.7 \mathrm{m}\Omega @ \mathrm{V_{GS}} = 2.5 \mathrm{V}$	17.5A		

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

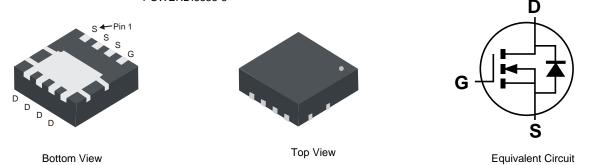
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS & Rg tested
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2005UFG-7	POWERDI3333-8	2,000/Tape & Reel
DMN2005UFG-13	POWERDI3333-8	3,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



N05= Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 13 = 2013) WW = Week Code (01 ~ 53)

POWERDI is a registered trademark of Diodes Incorporated DMN2005UFG Document number: DS36943 Rev. 3 - 2

1 of 7 www.diodes.com

POWERDI3333-8



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note C) // 45)/	Steady State	T _C = +25°C T _C = +70°C	ID	18.1 14.5	А
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	t<10s	T _A = +25°C T _A = +70°C	ID	24.1 19.3	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	58.3	A		
Maximum Continuous Body Diode Forward Current	ls	2.6	A		
Avalanche Current , L = 0.2mH			I _{AS}	23.9	A
Repetitive Avalanche Energy, L = 0.2mH			E _{AS}	58.4	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.05	W
Thermal Decisioner, Junction to Ambient (Note 5)	Steady state	5	120	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ extsf{ heta}JA}$	67	
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.27	W
Thermal Desistance, Junction to Ambient (Note 6)	Steady state	5	55	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	31	
Thermal Resistance, Junction to Case (Note 6)	$R_{ ext{ heta}JC}$	6.1		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Notes:

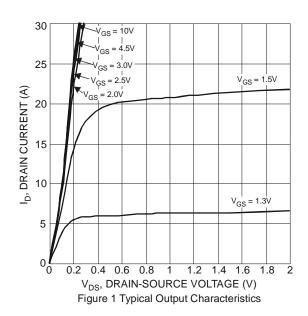
Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

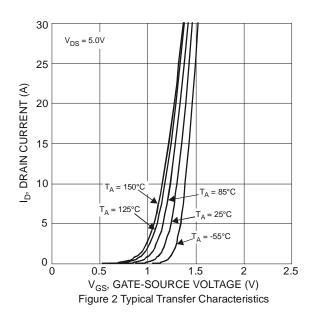


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	_	10	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	—	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.4	0.7	1.2	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	4	4.6	mΩ	V _{GS} = 4.5V, I _D = 13.5A	
Static Drain-Source On-Resistance	R _{DS} (ON)		4.9	8.7	mΩ	V _{GS} = 2.5V, I _D = 13.5A	
Diode Forward Voltage	V _{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_{S} = 27A$	
DYNAMIC CHARACTERISTICS (Note 8)			•	•	•		
Input Capacitance	Ciss	—	6,495	_	pF		
Output Capacitance	Coss	—	546	_	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	—	477	_	pF		
Gate Resistance	Rg	—	0.7	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	—	68.8	—	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	—	164	—	nC		
Gate-Source Charge	Q _{gs}		10.4	_	nC	V _{DS} = 16V, I _D = 27A	
Gate-Drain Charge	Q _{gd}		17.4	_	nC	1	
Turn-On Delay Time	t _{D(on)}		12.4	_	ns	$V_{GS} = 5V, V_{DS} = 10V,$ $R_G = 4.7\Omega, I_D = 13.5A$	
Turn-On Rise Time	tr		25.7		ns		
Turn-Off Delay Time	t _{D(off)}	—	114	_	ns		
Turn-Off Fall Time	t _f		38	_	ns		
Body Diode Reverse Recovery Time	t _{rr}	—	16.1	—	ns	I _F = 13.5A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{rr}	_	8.5	_	nC	I _F = 13.5A, di/dt = 100A/µs	

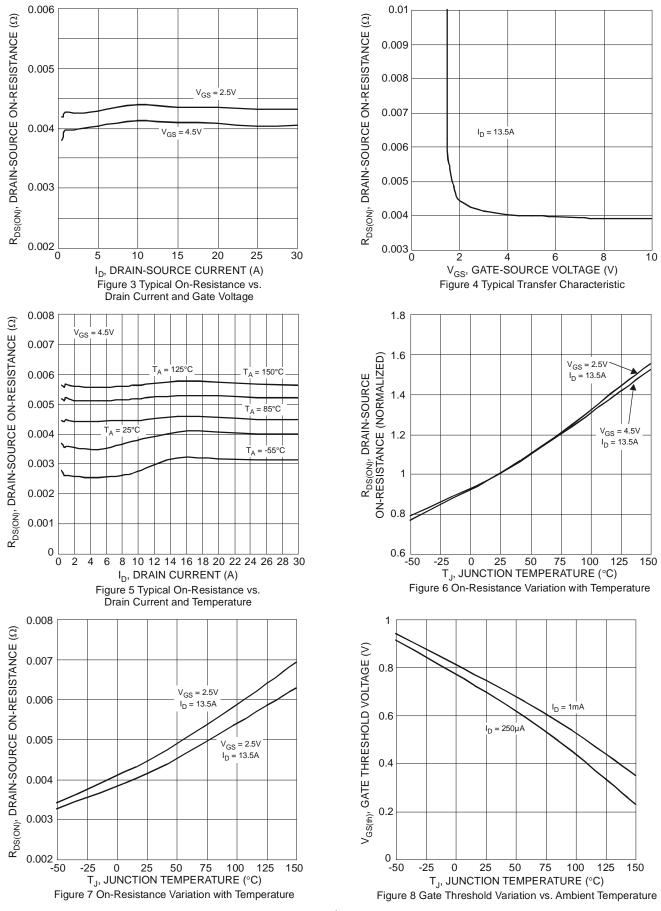
Notes: 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







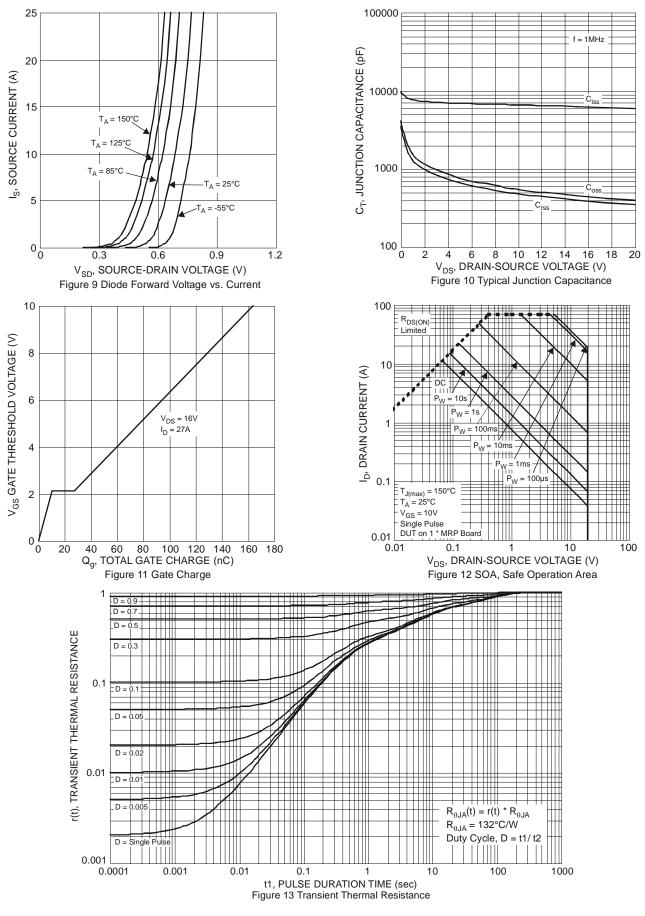
DMN2005UFG



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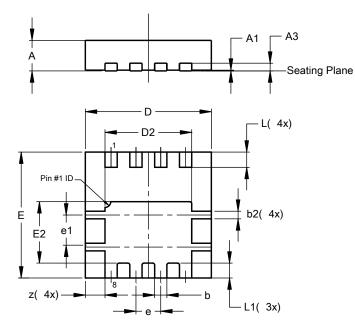
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Package Outline Dimensions

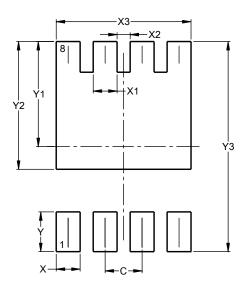
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



POWERDI [®] 3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	_	-	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
е	-	-	0.65			
e1	0.79	0.89	0.84			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	-	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
X3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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